

Supporting Information

High-responsivity solution-processed organic-inorganic hybrid bilayer thin film photoconductors

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1. FET performances of the used films

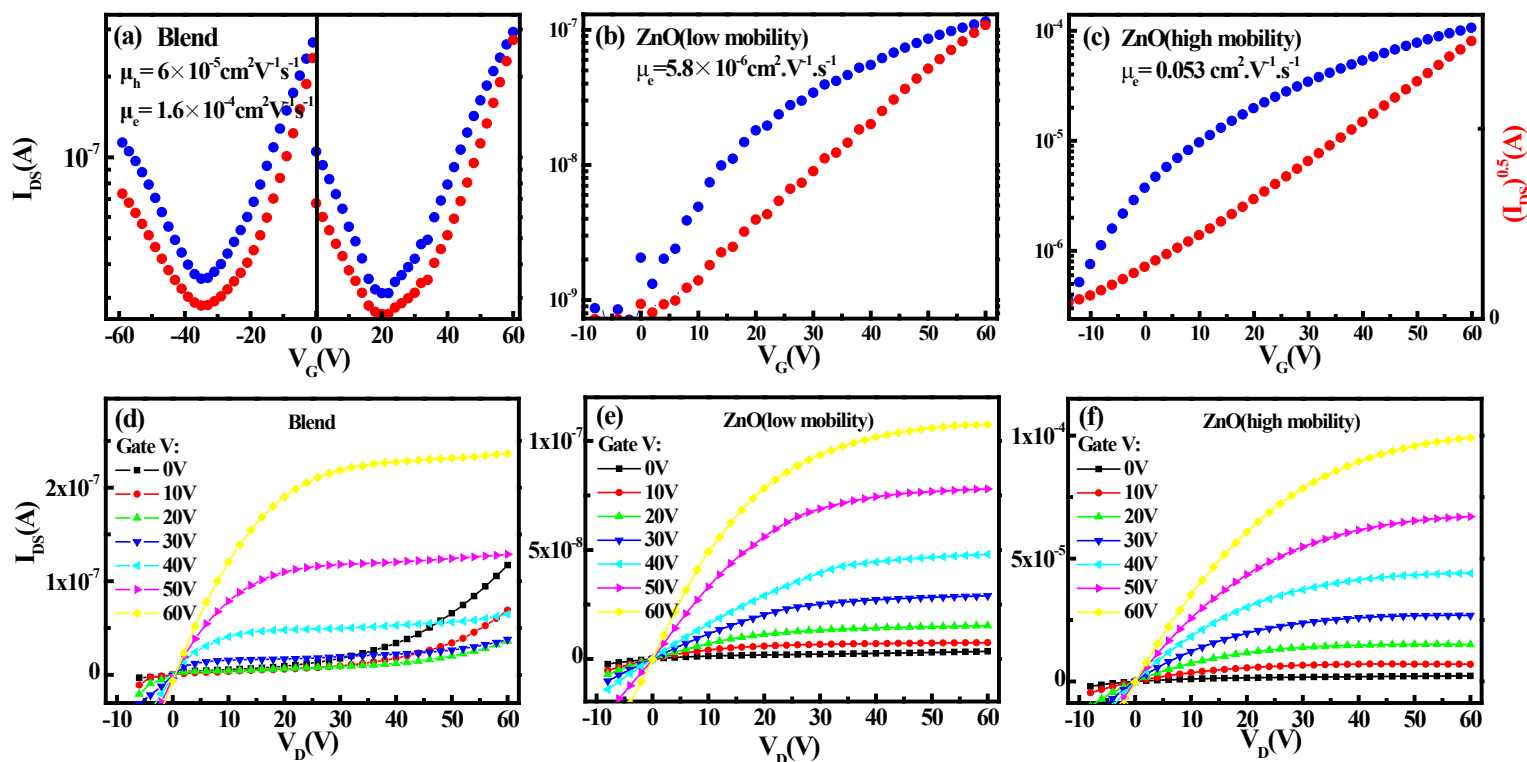


Figure S1. The FET performances of the used films. (a) and (d) : P3HT:PCBM blend film. (b) and (e): the low-mobility ZnO film. (c) and (f): the high-mobility ZnO film. (The thin-film transistors were fabricated by directly spin-coating the active layer on SiO_2 (300 nm)/ Si^+ substrates, followed by thermal deposition of 50 nm-thick Al electrodes via a shadow mask, resulting in a channel width of 8800 μm and a channel length of 80 μm .)

2. Molecular structures of the used organic materials

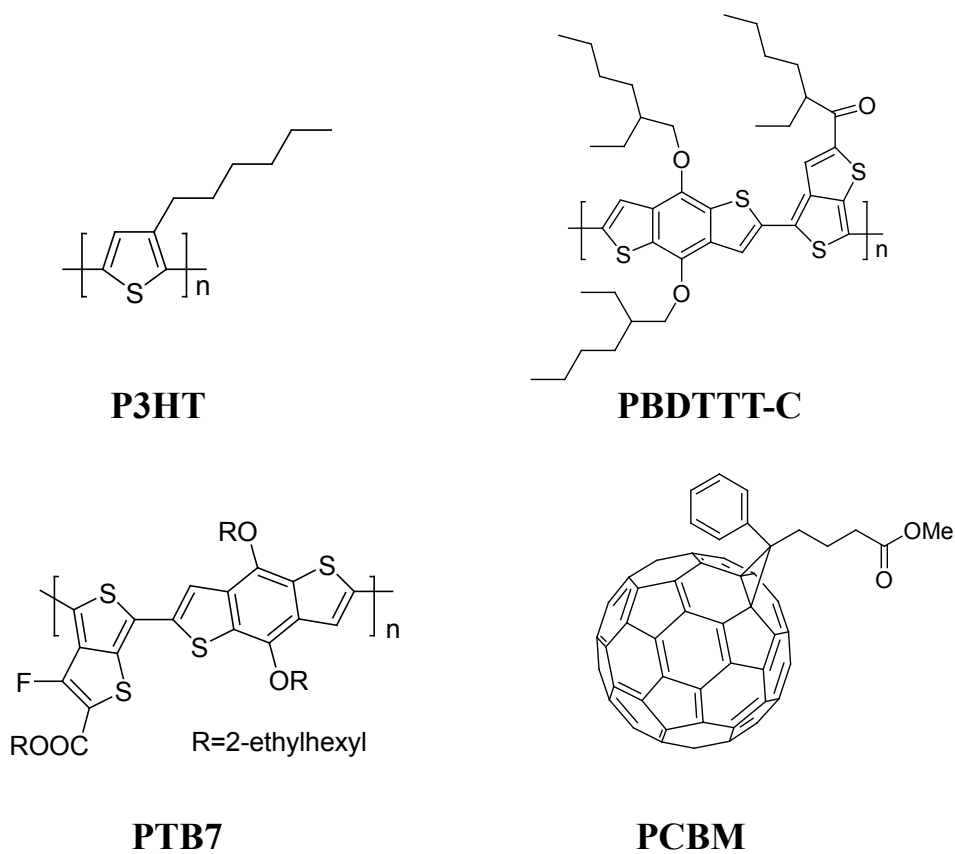


Figure S2. The molecular structures of the used organic materials.

3. Absorption spectra of the used organic films

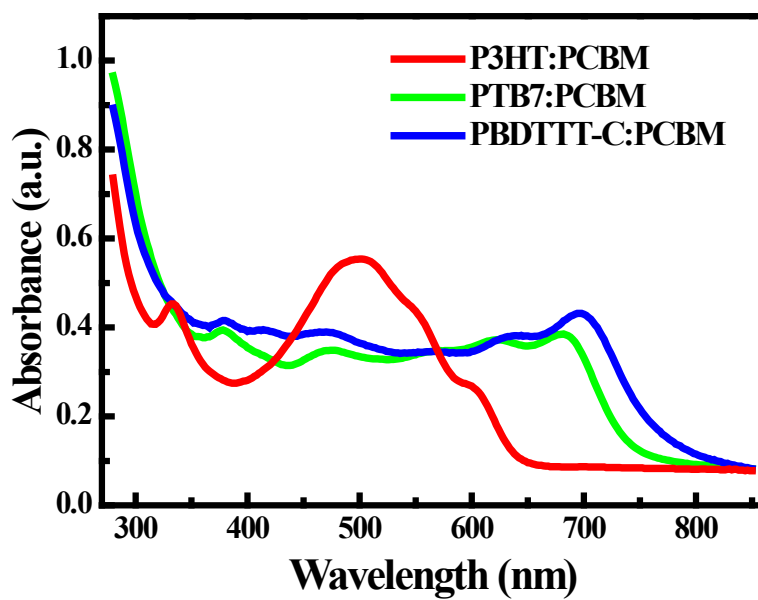


Figure S3. Absorption spectra of the used materials (P3HT: PCBM film , PTB7: PCBM film and PBDTTT-C: PCBM film).